USB Host Charger Identification Analog Switches



General Description

The SLG55594/SLG55594A is a USB device that combines high speed USB switches with a USB host charger (dedicated charger) identification circuit. The device supports both the latest USB Battery Charging Specification Revision 1.2 including data contact detection and a set resistor bias for Apple* compliant devices as well as legacy USB D+/D- short detection using data line pull-up.

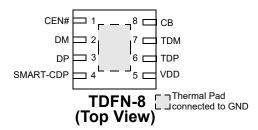
The SLG55594/SLG55594A can also support CDP mode (FAST charging and data communication available mode if smartphone can support CDP mode.)

The SLG55594/SLG55594A can also support low speed / full speed mouse/keyboard wake-up from S3 mode.

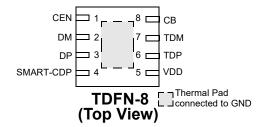
Features

- · High Speed USB Switching
- Low 4.0pF (typ) On Capacitance
- Low 4.0Ω (typ) On Resistance
- Low 0.5Ω (typ) On Resistance Flatness
- 4.5V to 5.5V Supply Range
- Low Supply Current
- · Automatic Current-Limit Switch Control
- Automatic USB Charger Identification Circuit
- CDP Support (active USB 2.0 data communication with 1.5A charging)
- Automatic CDP/SDP mode support with SMART-CDP=1 for "Always Data Communication"
- Chinese Telecom Standard YD/T 1591-2009 specification support
- · Samsung Galaxy Tab** charge scheme support
- · Pb-Free / RoHS Compliant / Halogen-Free
- TDFN-8 Package

Pin Configuration - SLG55594

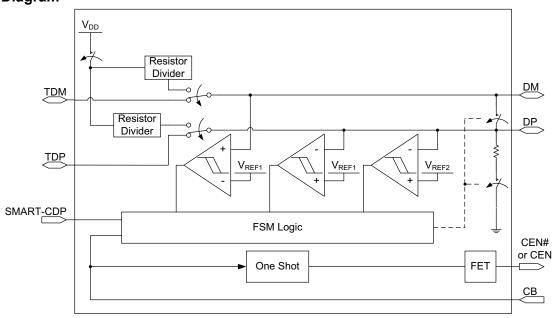


Pin Configuration - SLG55594A



- * Apple iPhone, iPad and iPod are trademarks of Apple Inc., registered in the U.S. and other countries.
- ** Samsung Galaxy Tab are trademarks of Samsung Electronics, registered in Korea and other countries.

Block Diagram





Pin Description - SLG55594

Pin #	Pin Name	Туре	Pin Description
1	CEN#	Output	P-FET Open Drain Output. Current Limit Switch (CLS) Control Output. CB changes from 0 to 1 or 1 to 0. CEN# will be high for 2 seconds (typ)
2	DM	Input/Output	USB Connector D-
3	DP	Input/Output	USB Connector D+
4	SMART-CDP	Input	Input Control logic (see truth table)
5	VDD	PWR	Power Supply. Connect a $0.1\mu\text{F}$ capacitor between VDD and GND as close as possible to the device.
6	TDP	Input/Output	Host USB Transceiver D+ Connection
7	TDM	Input/Output	Host USB Transceiver D- Connection
8	СВ	Input	Switch Control Bit 0 = autodetection charger identification active 1 = charging downstream port with active USB2.0 data communication mode with 1.5A support
9	Thermal Pad	GND	Ground

Pin Description - SLG55594A

Pin#	Pin Name	Туре	Pin Description
1	CEN	Output	N-FET Open Drain Output. Current Limit Switch (CLS) Control Output. CB changes from 0 to 1 or 1 to 0. CEN will be low for 2 seconds (typ)
2	DM	Input/Output	USB Connector D-
3	DP	Input/Output	USB Connector D+
4	SMART-CDP	Input	Input Control logic (see truth table)
5	VDD	PWR	Power Supply. Connect a $0.1\mu F$ capacitor between VDD and GND as close as possible to the device.
6	TDP	Input/Output	Host USB Transceiver D+ Connection
7	TDM	Input/Output	Host USB Transceiver D- Connection
8	СВ	Input	Switch Control Bit 0 = autodetection charger identification active 1 = charging downstream port with active USB2.0 data communication mode with 1.5A support
9	Thermal Pad	GND	Ground

Truth Table

СВ	SMART-CDP	Function
0	Х	DCP autodetect with mouse/keyboard wakeup
1	0	S0 charging with SDP only
1	1	S0 charging with CDP or SDP only (depending on external device) And, when Non-CDP phone is plugged in, the CDP mode will be changed automatically to SDP mode during handshaking protocol for supporting data communication.

Ordering Information

Part Number	Туре
SLG55594V	TDFN-8
SLG55594VTR	TDFN-8 - Tape and Reel
SLG55594AV	TDFN-8
SLG55594AVTR	TDFN-8 - Tape and Reel

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Absolute Maximum Ratings

Parameter	Min.	Max.	Unit
Supply Voltage	-0.3	6.0	V
Continuous Current into any terminal	-30	+30	mA
Continuous Power Dissipation		954	mW
Operating Temperature Range	-40	85	°C
Junction Temperature		150	°C
Storage Temperature Range	-65	150	°C
Lead Temperature (Soldering, 10s)		260	°C

Note: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Electrical Characteristics - Power Supply

 V_{DD} = 4.5V to 5.5V, T_A = 25°C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
W	Power Supply Range	V _{CB} > V _{IH}	4.5	5.0	5.5	V
V DD		V _{CB} = 0V	4.75		5.25	V
V _{DD}		CB = LOW, SMART-CDP = X (autodetect with wakeup)		120	140	μΑ
		CB = HIGH, SMART- = LOW (SDP)		20	30	μΑ
		CB = HIGH, SMART- = HIGH (CDP)		40	70	μΑ

Electrical Characteristics - Analog Switch

 V_{DD} = 4.5V to 5.5V, T_A = 25°C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
V_{DP}, V_{DM}	Analog signal Range		0		V_{DD}	V
D.	On Resistance TDP/TDM Switch	V _{DP/DM} = 0 V, I _{DP/DM} = 30 mA		2	4	Ω
R _{ON}	Officesistance FDF / FDM Switch	V _{DP/DM} = 2.4 V, I _{DP/DM} = -15 mA		3	6	Ω
ΔR_{ON}	On Resistance Match between channels TDP/TDM Switch	$V_{DD} = 5 V$ $V_{DP} = V_{DM} = 400 \text{ mV}$ $I_{DP} = I_{DM} = 10 \text{ mA}$		0.1		Ω
R _{FLAT}	On Resistance flatness TDP/TDM Switch	$V_{DD} = 5.0V$ $V_{DP} = V_{DM} = 0V \text{ to } V_{DD}$ $I_{DP} = I_{DM} = 10\text{mA}$		0.5		Ω
R _{SHORT}	On Resistance of TDP/TDM Short	$V_{CB} = 0V$ $V_{DP} = 1V$ $I_{DP} = I_{DM} = 10mA$		50	70	Ω
I _{TDPOFF} , I _{TDMOFF}	Off-Leakage Current	$V_{DD} = 3.6V$ $V_{DP} = V_{DM} = 0.3V \text{ to } 3.3V$ $V_{TDP} = V_{TDM} = 3.3V \text{ to } 0.3V$ $V_{CB} = 0V$	-250		250	nA

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 V_{DD} = 4.5V to 5.5V, T_A = 25°C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
I _{DPON} , I _{DMON}	Off-Leakage Current	$V_{DD} = 3.6V$ $V_{DP} = V_{DM} = 3.3V$ to 0.3V $V_{CB} = V_{DD}$	-250	ı	250	nA

Electrical Characteristics - Dynamic Performance

 V_{DD} = 4.5V to 5.5V, T_A = 25°C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
T _{ON}	Turn On Time	V_{TDP} or V_{TDM} = 1.5V R_L = 300 Ω C_L = 35pF	'	20	100	μs
T _{OFF}	Turn Off Time	V_{TDP} or V_{TDM} = 1.5V R_L = 300 Ω C_L = 35pF	'	1	5	μs
T _{PLH} , T _{PHL}	TDP/TDM Switch Propagation Delay	$R_L = R_S = 50\Omega$		60		ps
T _{SKEW}	Output Skew	Skew between DP and DM when connected to TDP and TDM $R_L = R_S = 50\Omega$		40		ps
C _{OFF}	TDP/TDM Off-Capacitance	f = 1MHz	"	2.0		pF
C _{ON}	DP/DM On-Capacitance	f = 240MHz	'	4.0	5.5	pF
BW	-3dB Bandwidth	$R_L = R_S = 50\Omega$		1000		MHz
V _{ISO}	Off-Isolation	$V_{TDP_1}V_{DP} = 0$ dBm $R_L = R_S = 5 0\Omega$ f = 250MHz		-20		dB
V _{CT}	Crosstalk	$V_{TDP_1}V_{DP} = 0$ dBm $R_L = R_S = 50\Omega$ f = 250MHz		-25		dB

Electrical Characteristics - Internal Resistors

 V_{DD} = 4.5V to 5.5V, T_A = 25°C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
R _{PD}	DP/DM Short Pull-down		350	500	700	kΩ
RT _{RP}	RP1/RP2 Ratio		1.485	1.5	1.515	Ratio
R _{RP}	RP1 + RP2 Resistance		93.75	125.0	156.25	kΩ
RT _{RM}	RM1/RM2 Ratio		0.8544	0.863	0.872	Ratio
R _{RM}	RM1 + RM2 Resistance		69.75	93.0	115.18	kΩ

Electrical Characteristics - Logic Input CB

 V_{DD} = 4.5V to 5.5V, T_A = 25°C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
V _{IH}	CB Input Logic High		1.4			V
V _{IL}	CB Input Logic Low				0.4	V
I _{IN}	CB Input Leakage Current	V_{DD} = 5.5V 0 \leq V _{CB} \leq V _{IL} or V _{IH} \leq V _{CB} \leq V _{DD}	-1	-	1	μΑ

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Electrical Characteristics - Logic Input SMART-CDP

 V_{DD} = 4.5V to 5.5V, T_A = 25°C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
V _{IH}	SMART-CDP input Logic High		3.0			V
V _{IL}	SMART-CDP input Logic Low				0.8	V
I _{IN}	SMART-CDP Input Leakage Current	V_{DD} = 5.5V $0V < V_{SMART-CDP} < V_{IL}$ or $V_{IH} < V_{SMART-CDP} < V_{DD}$	-1		1	μΑ

Electrical Characteristics - CEN#/CEN Outputs

 V_{DD} = 4.5V to 5.5V, T_A = 25°C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
T _{VBT}	V _{BUS} Toggle Time	CB = Logic 0 to Logic 1 or Logic 1 to Logic 0	1.5	2.0	2.5	s
V _{OH_CEN#}	CEN# Output Logic High Voltage CB = Logic 0 to Logic 1 I _{SOURCE} = 2mA		V _{DD} -0.4V			V
I _{OUT_CEN#}	CEN# Output Leakage Current	V _{DD} = 5.5V V _{CEN#} = 0V or CEN# deasserted		-	1	μΑ
V _{OL_CEN}	CEN Output Logic Low Voltage	CB = Logic 0 to Logic 1 I _{SINK} = 2mA			0.4V	٧
I _{OUT_CEN}	CEN Output Leakage Current	V _{DD} = 5.5V V _{CEN} = 5.5V or CEN deasserted			1	μΑ

Electrical Characteristics - ESD Protection

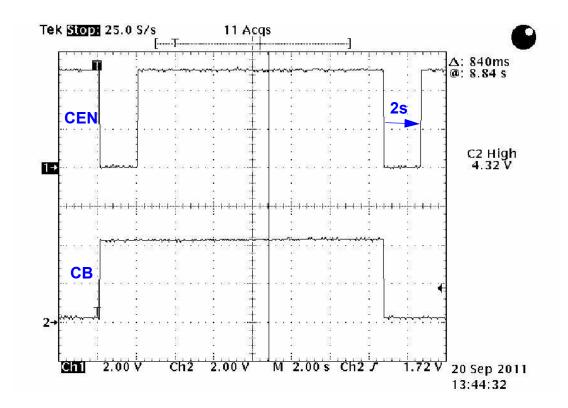
 V_{DD} = 4.5V to 5.5V, T_A = 25°C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
V _{ESD}	ESD Protection Level (DP and DM Only)	Human Body Model		±8		kV
V _{ESD}	ESD Protection Level (All other pins)	Human Body Model		±2		kV

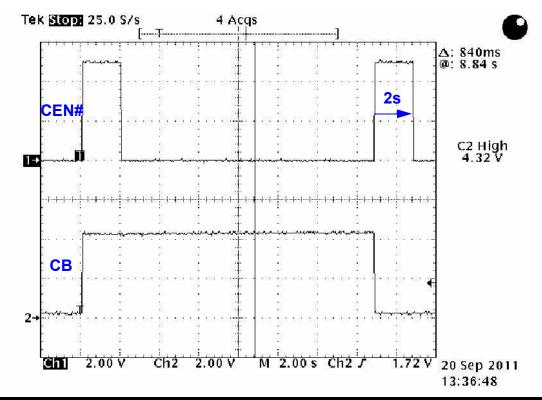
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CEN Function Waveform



CEN# Function Waveform



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Package Top Marking System Definition

	8 7 6 5	
Part ID	XXA	Assembly Code
Datecode	DD L	Lot
	<u>R</u>	Revision
	1 2 3 4	

XX - Part ID Field: identifies the specific device configuration

A - Assembly Code Field: Assembly Location of the device.

DD - Date Code Field: Coded date of manufacture

L - Lot Code: Designates Lot #

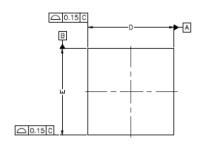
R - Revision Code: Device Revision

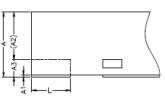
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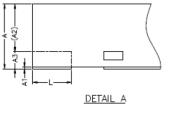


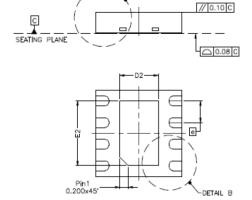
Package Drawing and Dimensions

8 Lead TDFN Package JEDEC MO-229, Variation WCCD

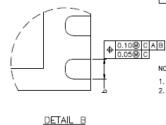








-DETAIL A



DIMENSION DIMENSION SYMBOL (MM) (MIL) MIN. NOM. MAX. MIN. NOM. MAX. 0.70 0.75 0.80 30 31 0.00 0.05 Α1 0.02 0 2 A2 0.55 0.80 0 22 31 0 АЗ 0.20 8 0.30 b 0.18 0.25 10 12 D 2.00 2.10 74 79 83 D1 D2 0.75 0.90 1.05 30 35 41 Ε 1.90 2.00 2.10 75 79 83 E1 E2 1.65 1.70 53 59 65 0.50 BSC 20 BSC е L 0.30 0.35 14

- REFER TO JEDEC STD: MO-229.
 DIMENSION "b" APPLIES TO METALLIZED TERMINAL AND IS MEASURED BETWEEN 0.15MM AND 0.30MM FROM THE TERMINAL TIP. IF THE TERMINAL HAS OPTIONAL RADIUS ON THE OTHER END OF THE TERMINAL, THE DIMENSION B SHOULD NOT BE MEASURED IN THAT RADIUS AREA.

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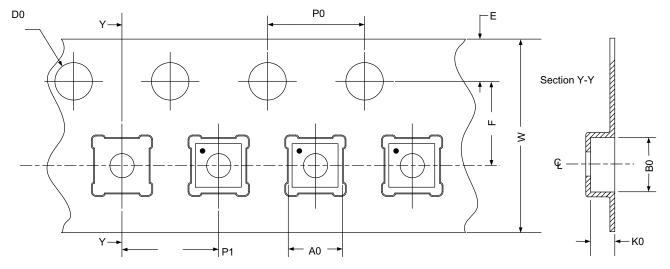


Tape and Reel Specifications

Package Type	# of Pins	Nominal Package Size [mm]	Max Units		Reel &	Leader (min)		Trailer (min)		Таре	Part
			per Reel	per Box	Hub Size [mm]	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
TDFN 8L Green	8	2 x 2 x 0.75	3,000	3,000	178 / 60	100	400	100	400	8	4

Carrier Tape Drawing and Dimensions

Package Type	PocketBTM Length	PocketBTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge		Tape Width	
	Α0	В0	K0	P0	P1	D0	E	F	w	
TDFN 8L Green	2.3	2.3	1.05	4	4	1.55	1.75	3.5	8	



Refer to EIA-481 specification

Recommended Reflow Soldering Profile

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of $3.00~\text{mm}^3$ (nominal). More information can be found at www.jedec.org.

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TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

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